

VN02H

HIGH SIDE SMART POWER SOLID STATE RELAY

TYPE	VDSS	R _{DS(on})	IOUT	Vcc
VN02H	60 V	0.4 Ω	6 A	36 V

- OUTPUT CURRENT (CONTINUOUS): 6A @ T_c=25°C
- 5V LOGIC LEVEL COMPATIBLE INPUT
- THERMAL SHUT-DOWN
- UNDER VOLTAGE SHUT-DOWN
- OPEN DRAIN DIAGNOSTIC OUTPUT
- VERY LOW STAND-BY POWER DISSIPATION

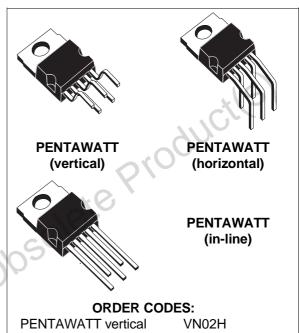
DESCRIPTION

The VN02H is a monolithic devices made using STMicroelectronics VIPower Technology, intended for driving resistive or inductive loads with one side grounded.

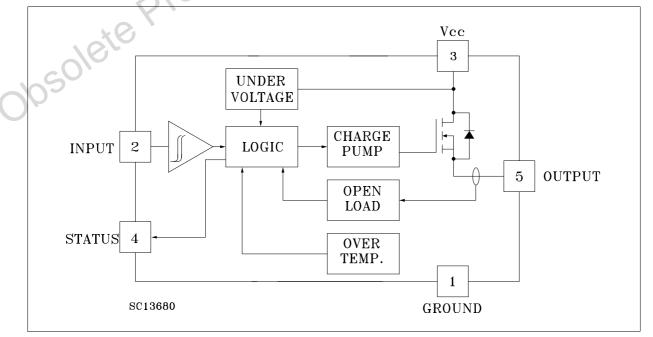
Built-in thermal shut-down protects the chip from over temperature and short circuit.

The input control is 5V logic level compatible. The open drain diagnostic output indicates open circuit (no load) and over temperature status.

BLOCK DIAGRAM



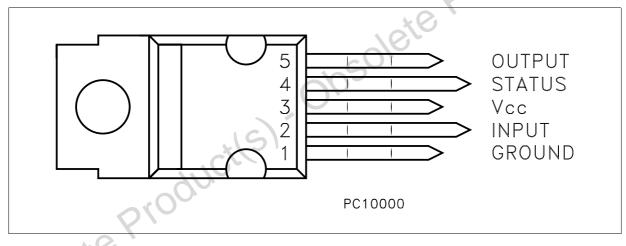
PENTAWATT horizontal PENTAWATT in-line VN02H(011Y) VN02H(012Y)



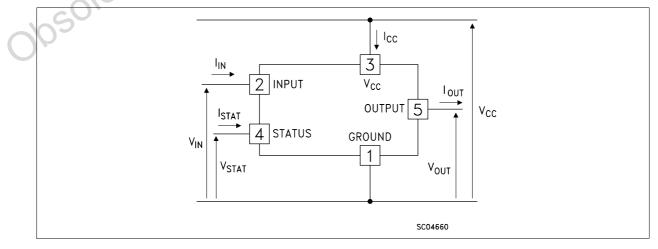
ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	60	V
I _{OUT}	Output Current (cont.)	6	А
I _R	Reverse Output Current	-6	А
l _{in}	Input Current	±10	mA
Vcc	Supply Voltage (for t = 400 ms)	60	V
-Vcc	Reverse Supply Voltage	-4	V
I _{STAT}	Status Current	±10	mA
Vesd	Electrostatic Discharge (1.5 kΩ, 100 pF)	2000	V
P _{tot}	Power Dissipation at $T_c \le 25$ °C	28) w
Tj	Junction Operating Temperature	-40 to 150	°C
T _{stg}	Storage Temperature	-55 to 150	°C

CONNECTION DIAGRAMS



CURRENT AND VOLTAGE CONVENTIONS



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THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	4.4	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	60	°C/W

ELECTRICAL CHARACTERISTICS (V_{CC} = 9 to 36 V; -40 \leq T_j \leq 125 °C unless otherwise specified) POWER

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	see note 1	5		36	V
Ron	On State Resistance	$I_{OUT} = 3 A$ $I_{OUT} = 3 A$ $T_j = 25 \ ^{\circ}C$			0.8 0.4	Ω Ω
Is	Supply Current	$\begin{array}{ll} \mbox{Off State} & T_j \geq 25 \ ^{o}\mbox{C} \\ \mbox{On State} & \end{array}$			50 20	μA mA
WITCHIN	IG			-91).05	

SWITCHING

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
t _{d(on)}	Turn-on Delay Time Of Output Current	$I_{OUT} = 3$ A Resistive Load Input Rise Time < 0.1 μ s T _j = 25 °C	5	10	20	μs
t _r	Rise Time Of Output Current	$I_{OUT} = 3$ A Resistive Load Input Rise Time < 0.1 μ s $T_j = 25$ °C	5	15	45	μs
$t_{d(off)}$	Turn-off Delay Time Of Output Current	$I_{OUT} = 3$ A Resistive Load Input Rise Time < 0.1 μ s T _j = 25 °C	5	15	30	μs
t _f	Fall Time Of Output Current	$I_{OUT} = 3$ A Resistive Load Input Rise Time < 0.1 μ s T _j = 25 °C	2	6	15	μs
(di/dt) _{on}	Turn-on Current Slope	louτ = 3 A louτ = lov 25 ≤ T _j ≤ 140 °C	0.05	0.15	0.5 2	A/μs A/μs
(di/dt) _{off}	Turn-off Current Slope	$I_{OUT} = 3 \text{ A}$ $I_{OUT} = I_{OV}$ $25 \le T_j \le 140 \text{ °C}$	0.1	0.4	2 4	A/μs A/μs
V_{demag}	Inductive Load Clamp Voltage	I _{OUT} = 3 A L = 1 mH	-7	-4	-2	V

LOGIC INPUT

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
VIL	Input Low Level Voltage				0.8	V
Vih	Input High Level Voltage		2		(*)	V
VI(hyst.)	Input Hysteresis Voltage			0.5		V
lin	Input Current	$V_{IN} = 5 V$		250	500	μA
VICL	Input Clamp Voltage	I _{IN} = 10 mA I _{IN} = -10 mA	5.5	6 -0.7	-0.3	V V

ELECTRICAL CHARACTERISTICS (continued)

PROTECTION AND DIAGNOSTICS

Symbol	Parameter	Test Co	nditions	Min.	Тур.	Max.	Unit
V _{STAT} (•)	Status Voltage Output Low	I _{STAT} = 1.6 mA				0.4	V
Vusd	Under Voltage Shut Down			2.5		5	V
V _{SCL} (•)	Status Clamp Voltage	I _{STAT} = 10 mA I _{STAT} = -10 mA		5.5	6 -0.7	-0.3	V V
t _{SC}	Switch-off Time in Short Circuit Condition at Start-Up	$R_{LOAD} < 10 m\Omega$ $T_c = 25 °C$	V _{CC} = 13 V		1.5	5	ms
lov	Over Current	R_{LOAD} < 10 m Ω	$V_{CC} = 13 V$			28	A
I _{AV}	Average Current in Short Circuit	$R_{LOAD} < 10 m\Omega$ $T_c = 85 °C$	V _{CC} = 13 V		0.9	1.8	A
I _{OL}	Open Load Current Level	9 < V _{CC} < 32 V		5	0	70	mA
Іоит	Leakage Current	Off State	Vout = 0 V			60	μA
T_{TSD}	Thermal Shut-down Temperature		10th	140	160		°C
T _R	Reset Temperature		cO'	125	145		°C

(*) The V_{IH} is internally clamped at 6V about. It is possible to connect this pin to an higher voltage via an external resistor calculated to not exceed 10 mA at the input pin.

(•) Status determination > 100 μ s after the switching edge.

Note 1 : Above V_{CC} = 36 V the output voltage is clamped to 36 V. Power dissipation increases and the device turns off if junction temperature reaches thermal shutdown temperature.

FUNCTIONAL DESCRIPTION

The device has a diagnostic output which indicates open circuit (no load) and over temperature conditions. The output signals are processed by internal logic.

To protect the device against short circuit and over-current condition the thermal protection turns the integrated Power MOS off at a minimum junction temperature of 140 °C. When the temperature returns to about 125 °C the switch is automatically turned on again. To ensur the protection in all V_{CC} conditions and in all the junction temperature range it is necessary to limit the voltage drop across Drain and Source (pin 3 and 5) at 29 V. The device is able to withstand a load dump according the test pulse 5 at level III of the ISO TR/1 7631.

Above $V_{CC} = 36V$ the output voltage is clamped to 36V. Power dissipation increases and the device turns off if junction temperature reaches thermal shutdown temperature.

PROTECTING THE DEVICE AGAINST REVERSE BATTERY

The simplest way to protect the device against a continuous reverse battery voltage (-26V) is to

insert a Schottky diode between pin 1 (GND) and ground, as shown in the typical application circuit (fig. 3).

The consequences of the voltage drop across this diode are as follows:

- If the input is pulled to power GND, a negative voltage of -V_F is seen by the device. (V_{IL}, V_{IH} thresholds and V_{STAT} are increased by V_F with respect to power GND).
- The undervoltage shutdown level is increased by V_F.

If there is no need for the control unit to handle external analog signals referred to the power GND, the best approach is to connect the reference potential of the control unit to node [1] (see application circuit infig. 4), which becomes the common signal GND for the whole control board.

In this way no shift of V_{IH} , V_{IL} and V_{STAT} takes place and no negative voltage appears on the INPUT pin; this solution allows the use of a standard diode, with a breakdown voltage able to handle any ISO normalized negative pulses that occours in the automotive environment.

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TRUTH TABLE

	INPUT	OUTPUT	DIAGNOSTIC
Normal Operation	L	L	H
	H	H	H
Open Circuit (No Load)	L	L	H
	H	H	L
Over-temperature	L	L	H
	H	H	L
Under-voltage	L H	L	H H

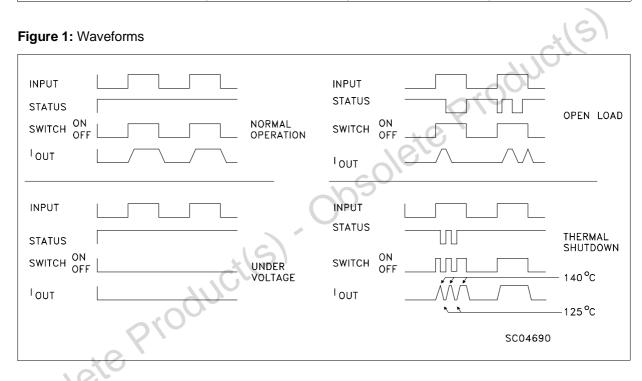
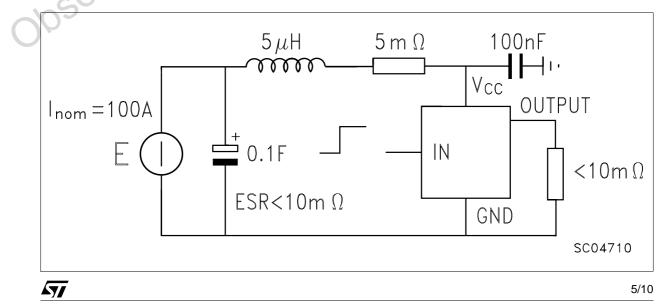
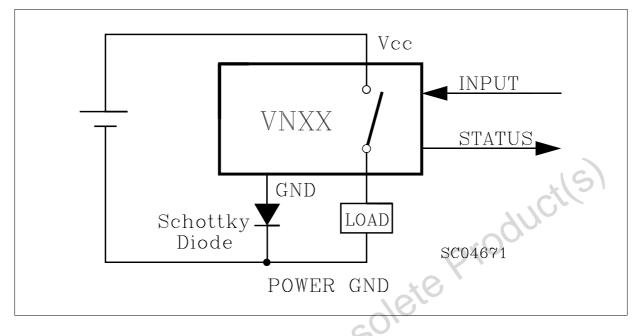


Figure 2: Over Current Test Circuit



VN02H



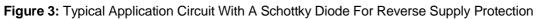
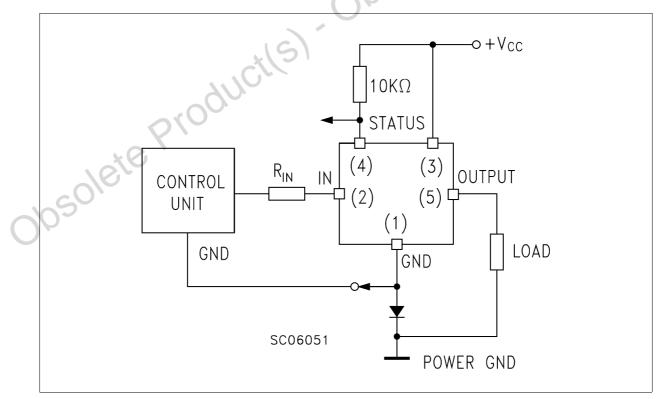


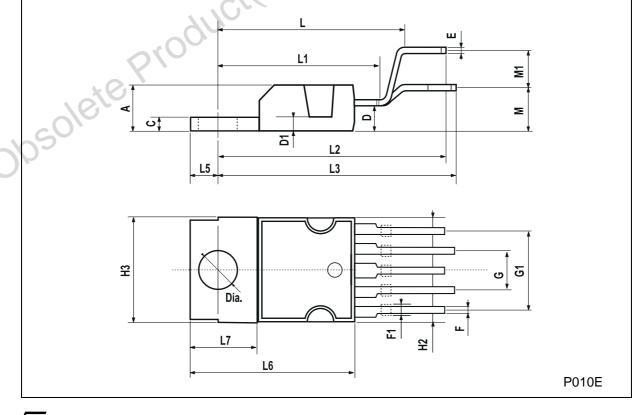
Figure 4: Typical Application Circuit With Separate Signal Ground



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DIM.		mm			inch	
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			4.8			0.189
С			1.37			0.054
D	2.4		2.8	0.094		0.110
D1	1.2		1.35	0.047		0.053
E	0.35		0.55	0.014		0.022
F	0.8		1.05	0.031		0.041
F1	1		1.4	0.039		0.055
G	3.2	3.4	3.6	0.126	0.134	0.142
G1	6.6	6.8	7	0.260	0.268	0.276
H2			10.4		11	0.409
H3	10.05		10.4	0.396		0.409
L		17.85			0.703	
L1		15.75			0.620	
L2		21.4		. 0.	0.843	
L3		22.5			0.886	
L5	2.6		3	0.102		0.118
L6	15.1		15.8 C	0.594		0.622
L7	6		6.6	0.236		0.260
М		4.5			0.177	
M1		4			0.157	
Dia	3.65		3.85	0.144		0.152

PENTAWATT (VERTICAL) MECHANICAL DATA



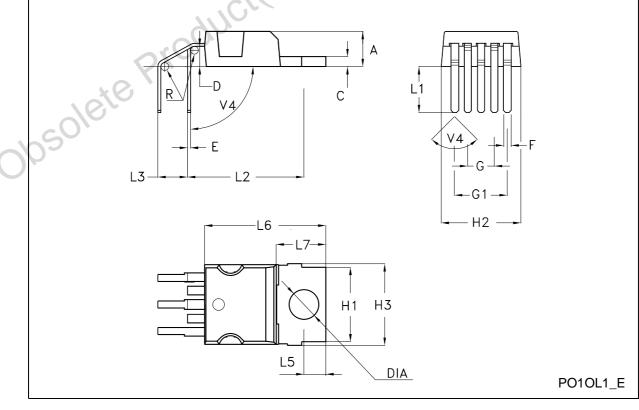
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PENTAWATT (HORIZONTAL) MECHANICAL DATA

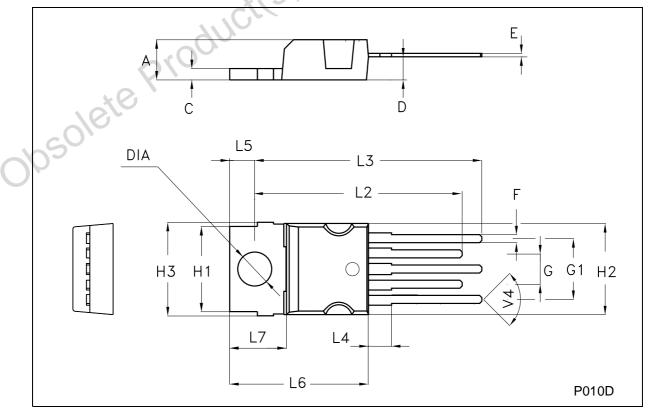
DIM.		mm			inch	
DIM.	MIN	ТҮР	МАХ	MIN	ТҮР	MAX
А	4.30		4.80	0.169		0.189
С	1.17		1.37	0.046		0.054
D	2.40		2.80	0.094		0.110
E	0.35		0.55	0.014		0.021
F	0.80		1.05	0.031		0.041
G	3.20		3.60	0.126		0.142
G1	6.60		7.00	0.260		0.275
H1	9.30		9.70	0.366	21)	0.382
H2			10.40			0.409
H3	10.05		10.40	0.396		0.409
L2	14.60		15.20	0.575	K i	0.598
L3	3.50		4.10	0.137		0.161
L5	2.60		3.00	0.102		0.118
L6	15.10		15.80	0.594		0.622
L7	6.00		6.60	0.236		0.260
V4		90°			90°	
Diam.	3.65		3.85	0.144		0.151



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DIM.		mm			inch		
Diwi.	MIN	ТҮР	MAX	MIN	TYP	MAX	
А	4.30		4.80	0.169		0.189	
С	1.17		1.37	0.046		0.054	
D	2.40		2.80	0.094		0.110	
E	0.35		0.55	0.014		0.021	
F	0.80		1.05	0.031		0.041	
F2	1.10		1.40	0.043		0.055	
F3	1.25		1.55	0.049		0.061	
G	3.20		3.60	0.126		0.142	
G1	6.60		7.00	0.260		0.275	
H1	9.30		9.70	0.366		0.382	
H2			10.40		-04	0.409	
H3	10.05		10.40	0.396		0.409	
L2	23.05		23.80	0.907		0.937	
L3	25.30		26.10	0.996		1.027	
L4	0.90		2.90	0.035		0.114	
L5	2.60		3.00	0.102		0.118	
L6	15.10		15.80	0.594		0.622	
L7	6.00		6.60	0.236		0.260	
V4		90°			90°		
Diam.	3.65		3.85	0.144		0.151	





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